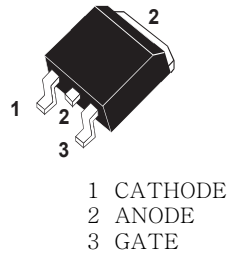


Silicon Planar PNP Thyristor (10A SCR)

MAIN FEATURES

Symbol	value	unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	600	V
I_{TSM}	100	A

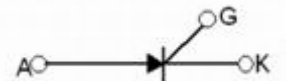


GENERAL DESCRIPTION

- Glass passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.
- Typical applications include motor control, industrial and domestic lighting, heating and static switching.

TO-263(D²PAK)

DIM	MILLIMETERS
A	10.1 ± 0.2
B	8.7 ± 0.2
D	15.3 ± 0.3
E	5.2 ± 0.2
F	2.54 ± 0.1
G	0.8 ± 0.1
I	4.5 ± 0.2
J	1.27 ± 0.13
L	0.5 ± 0.15
O	2.5 ± 0.3



ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

symbol	parameter			value	unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-252	$T_C=107^\circ\text{C}$	10	A
I_{TSM}	Non repetitive surge peak on-state current (full sine wave, $T_J=25^\circ\text{C}$)		$t=10\text{ms}$	100	A
			$t=8.3\text{ms}$	110	
I_{GM}	Peak gate current			4	A
$P_{G(AV)}$	Average gate power dissipation		$T_J=125^\circ\text{C}$	0.5	W
T_{stg}	Storage junction temperature range			-40 to +150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to +125	

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Rated repetitive peak off-state/reverse voltage	V_{DRM}, V_{RRM}	$I_D=10\mu\text{A}$	600		V
Rated repetitive peak off-state current	I_{DRM}, I_{RRM}	$V_D=620\text{V}$		10	μA
On-state voltage	V_{TM}	$I_T=23\text{A}$	1.4	1.75	V
Gate trigger current	I_{GT}	$V_D=12\text{V}$ $I_T=0.1\text{A}$ $R_L=100\Omega$		15	mA
Gate trigger voltage	V_{GT}	$V_D=12\text{V}$ $I_T=0.1\text{A}$ $R_L=100\Omega$		1.45	V
Holding current	I_H	$I_T=100\text{mA}$ $I_G=20\text{mA}$		20	mA

Typical Characteristics

Figure 1: Maximum average power dissipation versus average on-state current

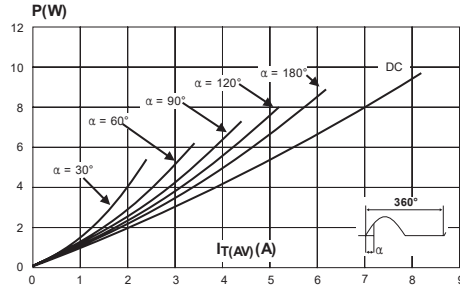


Figure 2: Correlation between maximum average power dissipation and maximum allowable temperature (T_{amb} and T_{lead})

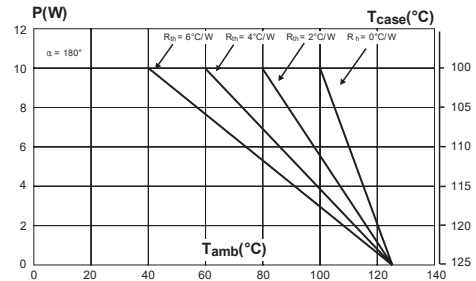


Figure 3: Average on-state current versus case temperature

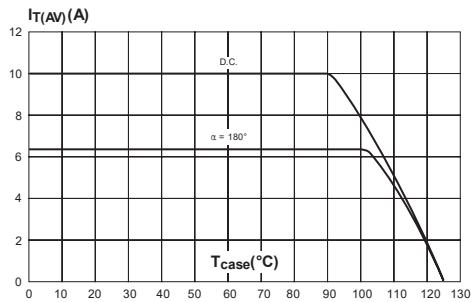


Figure 4: Relative variation of thermal impedance versus pulse duration

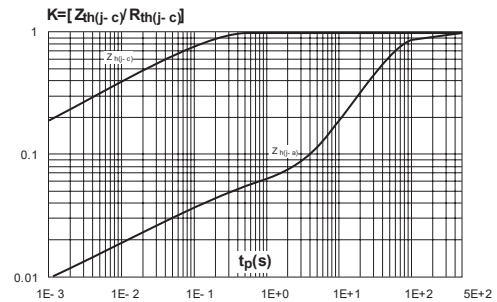


Figure 5: Relative variation of gate trigger current versus junction temperature

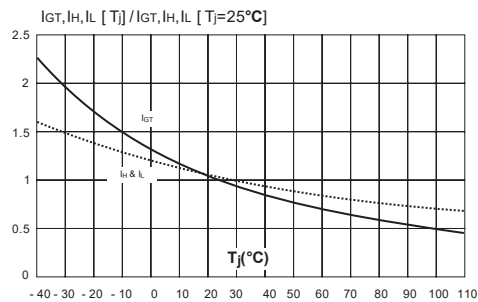


Figure 6: Surge peak on-state current versus number of cycles

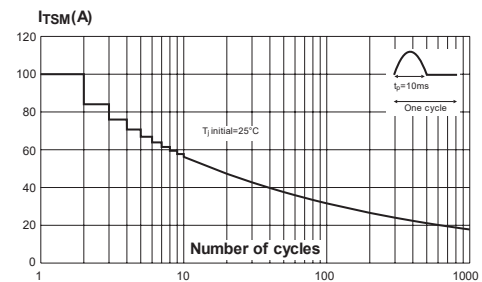


Figure 7: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms, and corresponding values of I^2t

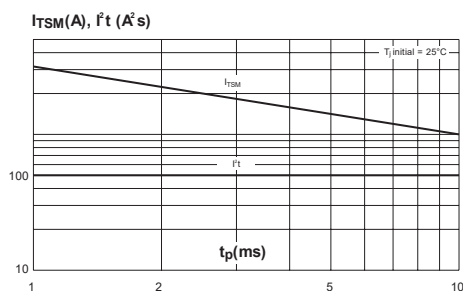


Figure 8: On-state characteristics (maximum values)

